



BTA08/BTB08 Series 8A TRIACs

DESCRIPTION:

High current density due to double mesa technology; SIPOS and Glass Passivation.

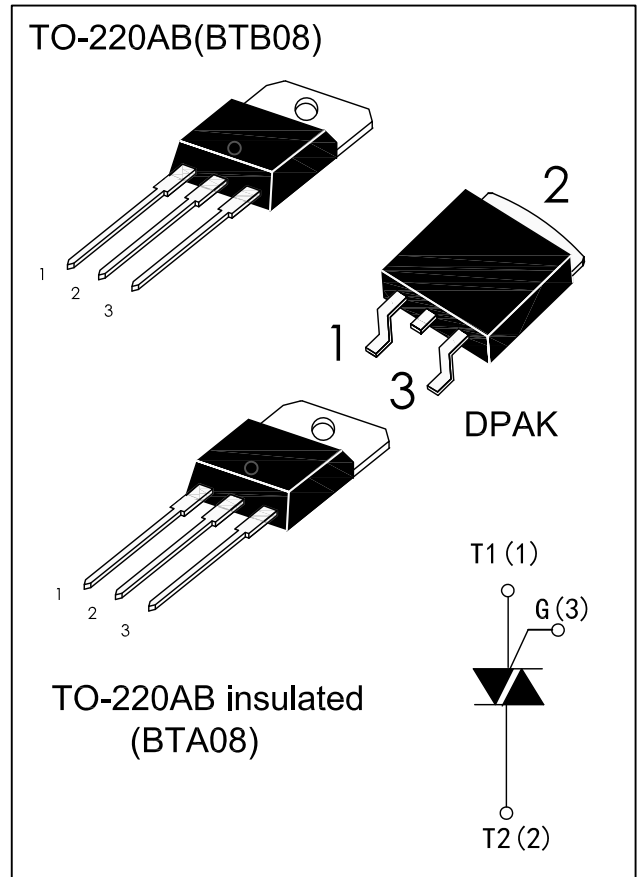
BTA08/BTB08 series triacs is suitable for general purpose AC switching. They can be used as an ON/OFF Function in applications such as static relays, heating regulation, induction motor starting circuits... or for phase control operation light dimmers, motorspeed controllers.

BTA08/BTB08- $\times\times\times$ SW, - $\times\times\times$ CW, - $\times\times\times$ BW are 3 Quadrants triacs, They are specially recommended for use on inductive loads.

BTA08 are isolated internally, they provides a 2500V RMS isolation voltage from all three terminals to external heatsink.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
V_{DRM}/V_{RRM}	600and800	V
V_{TM}	≤ 1.55	V



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	Tstg	-40 to +150	$^{\circ}\text{C}$
Operating junction temperature range	Tj	-40 to +125	$^{\circ}\text{C}$
Repetitive Peak Off-state Voltage Repetitive Peak Reverse Voltage	V_{DRM} V_{RRM}	600and800 600and800	V
Non repetitive Surge Peak Off-state Voltage Non repetitive Peak Reverse Voltage	V_{DSM} V_{RSM}	700and900 700and900	V
RMS on-state current (full sine wave)	DPAK / TO-220AB Tc=110 $^{\circ}\text{C}$	8	A
	TO-220AB Ins Tc=100 $^{\circ}\text{C}$		
Non repetitive surge peak on-state current (full cycle, Tj=25 $^{\circ}\text{C}$)	f = 50 Hz t=20ms	80 84	A
	f = 60 Hz t=16.7ms		
I ² t Value for fusing tp=10ms	I ² t	36	A ² s
Critical rate of rise of on-state current IG=2 \times IGT, tr \leq 100 ns, f=120Hz, Tj=125 $^{\circ}\text{C}$	di /dt	50	A/us
Peak gate current tp=20us, Tj=125 $^{\circ}\text{C}$	IGM	4	A
Average gate power dissipation Tj=125 $^{\circ}\text{C}$	PG(AV)	1	W

ELECTRICAL CHARACTERISTICS (T_j=25°C unless otherwise specified)

● 3 Quadrants

Symbol	Test Condition	Quadrant		BTA08/BTB08			Unit
				SW	CW	BW	
I _{GT}	V _D =12V R _L =30Ω	I - II - III	MAX.	10	35	50	mA
V _{GT}		I - II - III	MAX.	1.3			V
V _{GD}	V _D =V _D RM R _L =3.3KΩ T _j =125°C	I - II - III	MIN..	0.2			V
I _L	I _G =1.2I _{GT}	I - III	MAX.	25	50	70	mA
		II		30	60	80	
I _H	I _T =100mA		MAX.	15	35	50	mA
dV/dt	V _D =67%V _D RM gate open T _j =125°C		MIN.	40	500	1000	V/μs
(dl/dt) _c	(dV/dt) c=0.1V/μs T _j =125°C		MIN.	5.4	----	----	A/ms
	(dV/dt) c=10V/μs T _j =125°C			2.8	----	----	
	Without snubber T _j =125°C			----	4.5	7.0	

● 4 Quadrants

Symbol	Test Condition	Quadrant		BTA08/BTB08		Unit
				C	B	
I _{GT}	V _D =12V R _L =30Ω	I - II - III IV	MAX.	25 50	50 100	mA
V _{GT}		ALL	MAX.	1.3		V
V _{GD}	V _D =V _D RM R _L =3.3KΩ T _j =125°C	ALL	MIN.	0.2		V
I _L	I _G =1.2I _{GT}	I - III - IV	MAX.	40	50	mA
		II		80	100	
I _H	I _T =100mA		MAX.	25	50	mA
dV/dt	V _D =67%V _D RM gate open T _j =125°C		MIN.	200	400	V/μs
(dl/dt) _c	(dV/dt) c=0.1V/μs T _j =125°C		MIN.	---	---	A/ms
	(dV/dt) c=10V/μs T _j =125°C			---	---	
	Without snubber T _j =125°C			---	---	

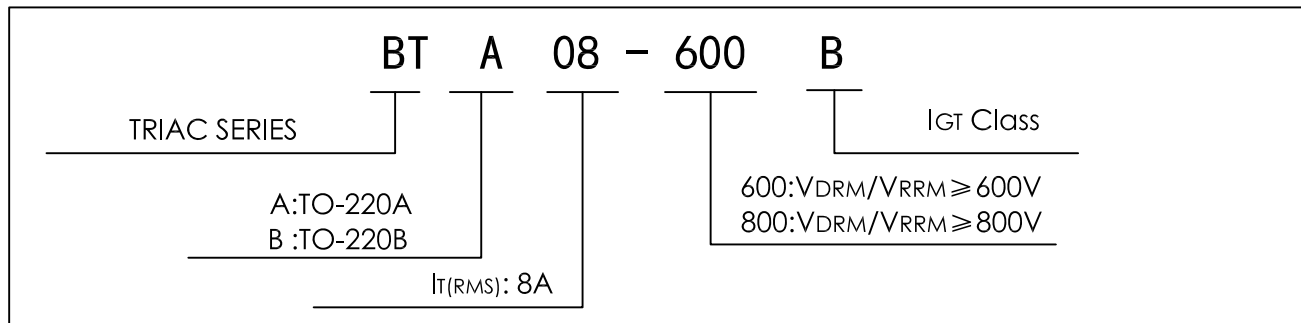
STATIC CHARACTERISTICS

Symbol	Test Conditions		Value (MAX)	Unit
V_{TM}	$I_{TM}=11A$, $t_p=380\mu S$	$T_j=25^\circ C$	1.55	V
I_{DRM}	$V_D=V_{DRM}$	$T_j=25^\circ C$	5	μA
I_{RRM}	$V_R=V_{RRM}$	$T_j=125^\circ C$	1	mA

THERMAL RESISTANCES

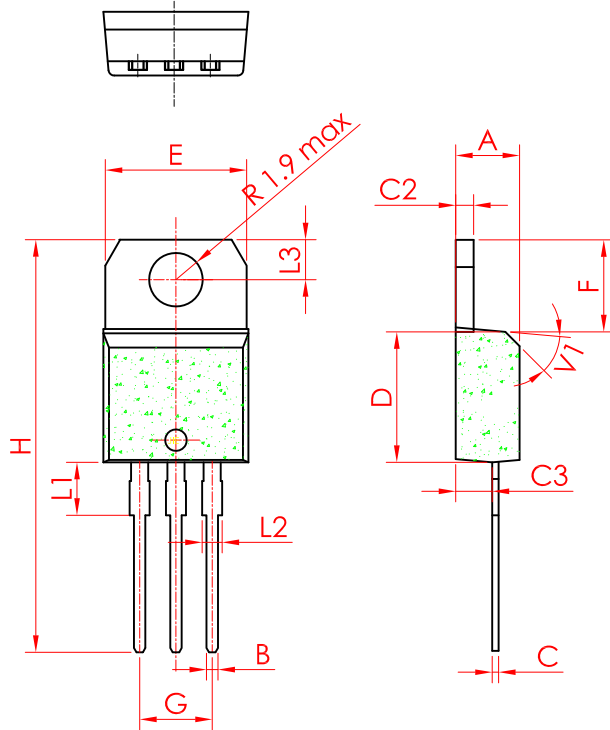
Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case (AC)	DPAK/TO-220AB	1.6	$^\circ C/W$
		TO-220AB Insulated	2.5	

ORDERING INFORMATION



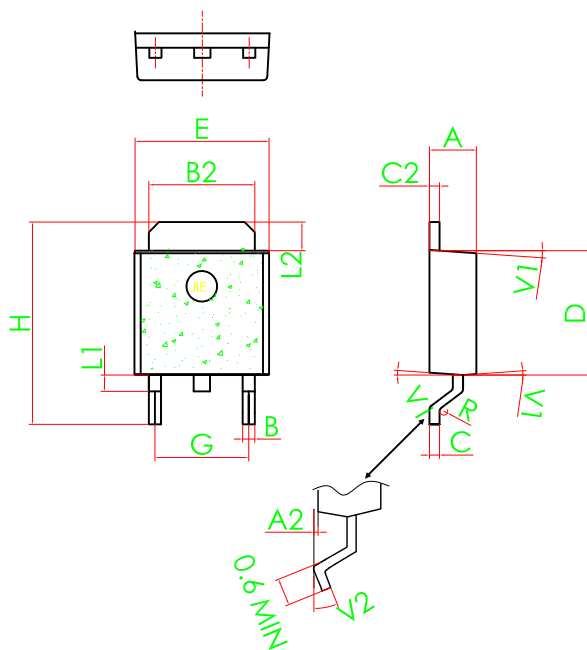
PACKAGE MECHANICAL DATA

TO-220AB



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.4		4.6	0.173		1.181
B	0.61		0.88	0.024		0.034
C	0.49		0.70	0.019		0.027
C2	1.23		1.32	0.048		0.051
C3	2.4		2.72	0.094		0.107
D	8.6		9.7	0.338		0.382
E	10		10.4	0.393		0.409
F	6.2		6.6	0.244		0.259
G	4.8		5.4	0.189		0.213
H	28.0		29.8	11.0		11.7
L1		3.75			0.147	
L2	1.14		1.7	0.044		0.066
L3	2.65		2.95	0.104		0.116
V1		40°			40°	

DPAK



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.2		2.4	0.086		0.095
A2	0.03		0.23	0.001		0.009
B	0.55		0.65	0.021		0.026
B2	5.2		5.4	0.204		0.212
C	0.45		0.62	0.017		0.024
C2	0.48		0.62	0.019		0.024
D	6		6.2	0.236		0.244
E	6.4		6.6	0.251		0.259
G	4.40		4.60	0.173		0.181
H	9.35		10.1	0.368		0.397
L1		0.8			0.031	
L2	1.37		1.5	0.054		0.059
V1		4°			4°	
V2		0°	8°		0°	8°

FIG.1: Maximum power dissipation versus RMS on-state current(full cycle)

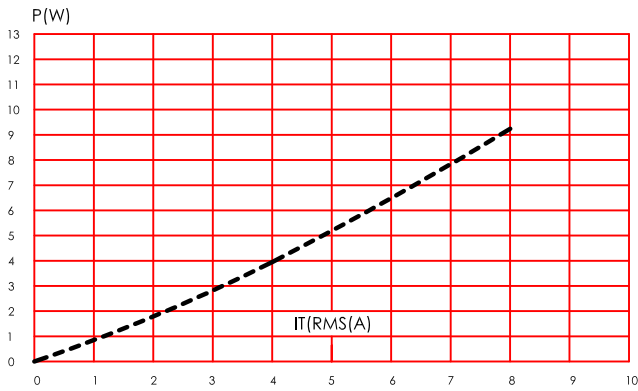


FIG.2: RMS on-state current versus case temperature(full cycle)

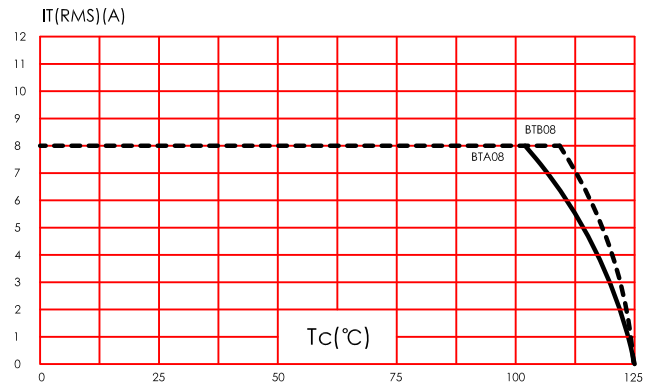


FIG.3: On-state characteristics (maximum values)

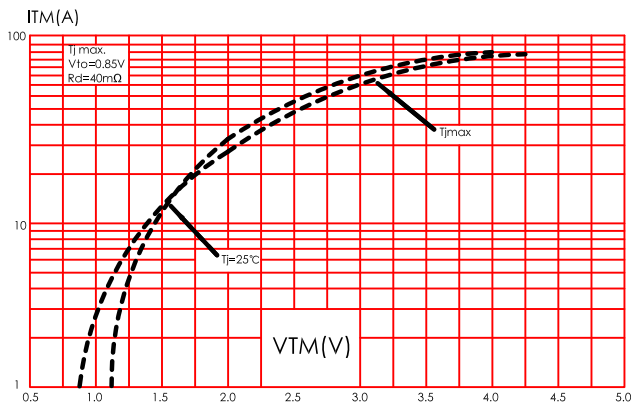


FIG.4: Surge peak on-state current versus number of cycles.

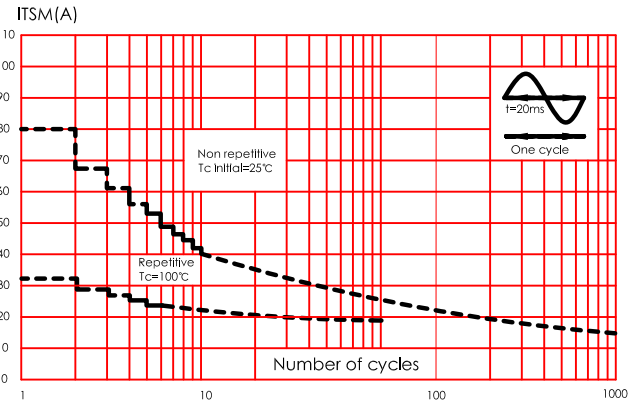


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t

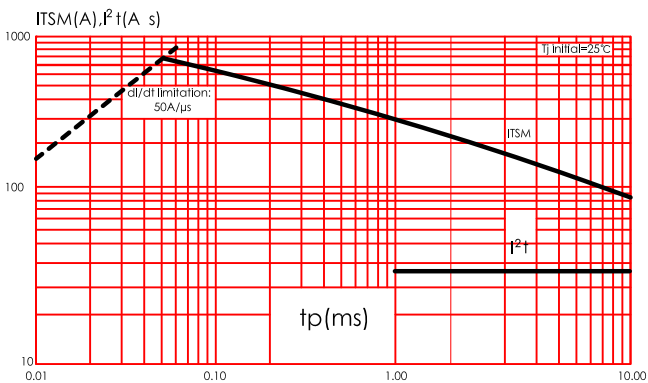


FIG.6: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values).

